

123. The semiconductor integrated circuit according to claim 113, wherein said first circuit has a second MOS transistor having a source-drain path with which said internal circuit makes a current path, and a feedback circuit between the gate of said second MOS transistor and the output of said first circuit.

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124. The semiconductor integrated circuit according to claim 113, wherein the load capacitance of said internal circuit changes in accordance with a signal.

125. The semiconductor integrated circuit according to claim 113, wherein the output of said second circuit is coupled to the output of said first circuit. --

REMARKS

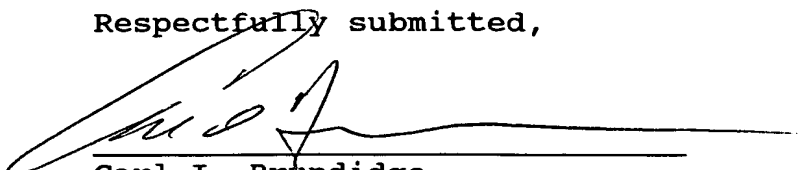
Favorable consideration of the above amendments is respectfully requested.

To the extent necessary, applicants petition for an extension of time under 37 C.F.R. section 1.136. Please charge any shortage in the fees due in connection with the filing of

this paper, including extension of time fees, to Deposit Account No. 01-2135 (Case No. 501.20699VC3) and please credit any excess fees to such Deposit Account.

Respectfully submitted,

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